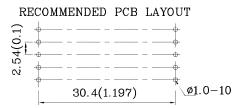
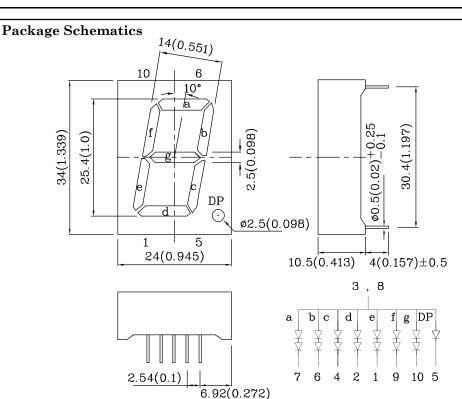


Features

- Low power consumption
- \bullet Robust package
- I.C. Compatible
- Standard configuration: Gray face w/ white segments
- Optional black face provides superior color contrast
- RoHS Compliant







Part Number: XDMDK25A

Notes: 1. All dimensions are in millimeters (inches), Tolerance is ± 0.25(0.01")unless otherwise noted. 2. Specifications are subject to change without notice.

Absolute Maximum Ratings (T _A =25°C)		MDK (AlGaInP)	Unit	
Reverse Voltage (Per Chip)	V_{R}	5	V	
Forward Current (Dp)	$I_{\rm F}$	30 (30)	mA	
Forward Current (Peak) 1/10 Duty Cycle 0.1ms Pulse Width (Dp)	ifs	185 (185)	mA	
Power Dissipation (Per Chip)	PD	75	mW	
Operating Temperature	$T_{\rm A}$	-40 ~ +85	°C	
Storage Temperature	Tstg	-40 ~ +85		
Lead Solder Temperature [2mm Below Package Base]	260°C For 3~5 Seconds			

Operating Characteristics (T _A =25°C)		MDK (AlGaInP)	Unit
Forward Voltage (Typ.) (Dp) (I _F =10mA)	$V_{\rm F}$	3.7 (1.85)	V
Forward Voltage (Max.) (Dp) (I _F =10mA)	$V_{\rm F}$	5 (2.5)	V
Reverse Current (Max.) (Per Chip) $(V_R=5V)$	I_R	10 (10)	uA
Wavelength of Peak Emission CIE127-2007* (Typ.) (I _F =10mA)	λP	645*	nm
Wavelength of Dominant Emission CIE127-2007* (Typ.) (I _F =10mA)	λD	630*	nm
Spectral Line Full Width At Half-Maximum (Typ.) (I _F =10mA)	$ riangle \lambda$	28	nm
Capacitance (Typ.) (V _F =0V, f=1MHz)	С	35	pF

Part Number	Emitting Color	Emitting Material	Luminous Intensity CIE127-2007* (IF=10mA) ucd		Wavelength CIE127-2007* Nm λΡ	Description
			min.	typ.		
XDMDK25A	Red	AlGaInP	88000 31000*	259990 69990*	645 *	Common Anode, Rt.Hand Decimal

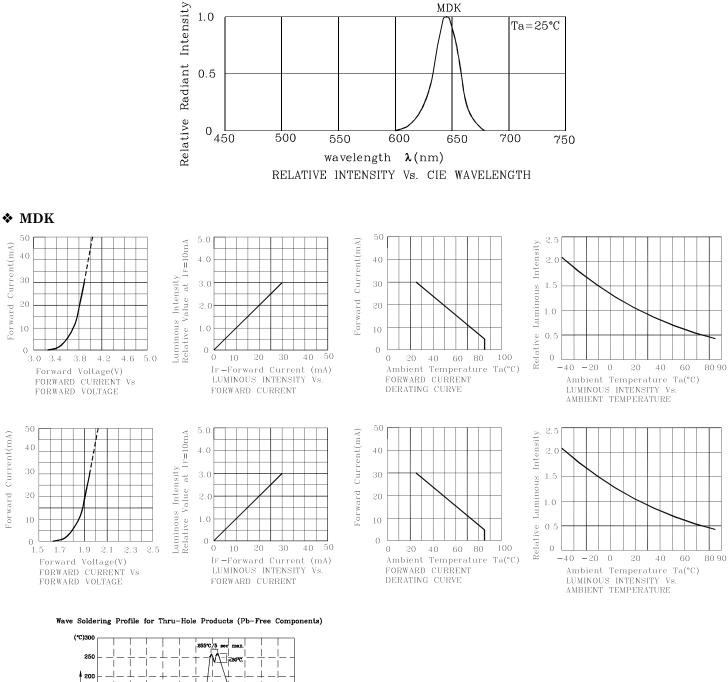
*Luminous intensity value and wavelength are in accordance with CIE127-2007 standards. Jan 18,2014

SDSA9239 V1-X Layout: Maggie L.

25.4mm (1.0 ") SINGLE DIGIT NUMERIC DISPLAY



25.4mm (1.0 ") SINGLE DIGIT NUMERIC DISPLAY



Remarks:

If special sorting is required (e.g. binning based on forward voltage, luminous intensity / luminous flux, or wavelength),

- the typical accuracy of the sorting process is as follows:
- 1. Wavelength: +/-1nm
- 2. Luminous Intensity / Luminous Flux: +/-15%
- 3. Forward Voltage: +/-0.1V

Note: Accuracy may depend on the sorting parameters.

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while the temperature is above component when mounting and

Time(sec)-

Notes: 1.Recommend pre-heat temperature of 105°C or less (as measured thermocouple attached to the LED pins) prior to immersion in th wave with a maximum solder bath temperature of 260°C 2.Peak wave soldering temperature between 245°C < 255°C for 3 sc max)

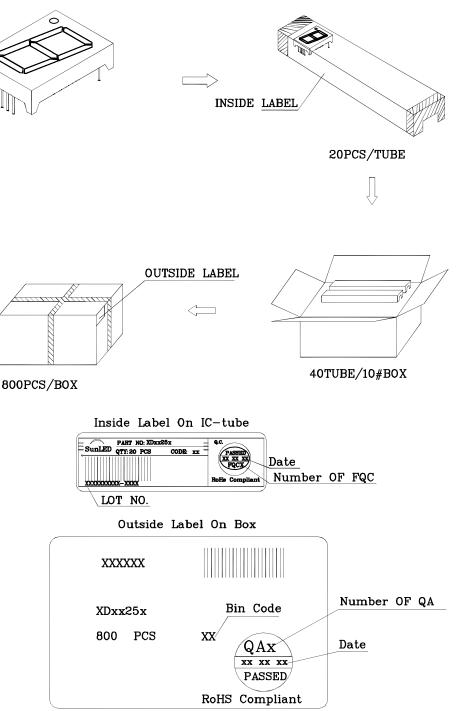
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Peak wave soldering temperature octave max).
3.Do not apply stress to the epoxy resin 4.Pixtures should not incur stress on the during soldering process.
5.SAC 305 solder alloy is recommended.
6.No more than one wave soldering pass.

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PACKING & LABEL SPECIFICATIONS



TERMS OF USE

- 1. Data presented in this document reflect statistical figures and should be treated as technical reference only.
- 2. Contents within this document are subject to improvement and enhancement changes without notice.
- 3. The product(s) in this document are designed to be operated within the electrical and environmental specifications indicated on the datasheet.
- User accepts full risk and responsibility when operating the product(s) beyond their intended specifications.
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